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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

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Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100mhdfb-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

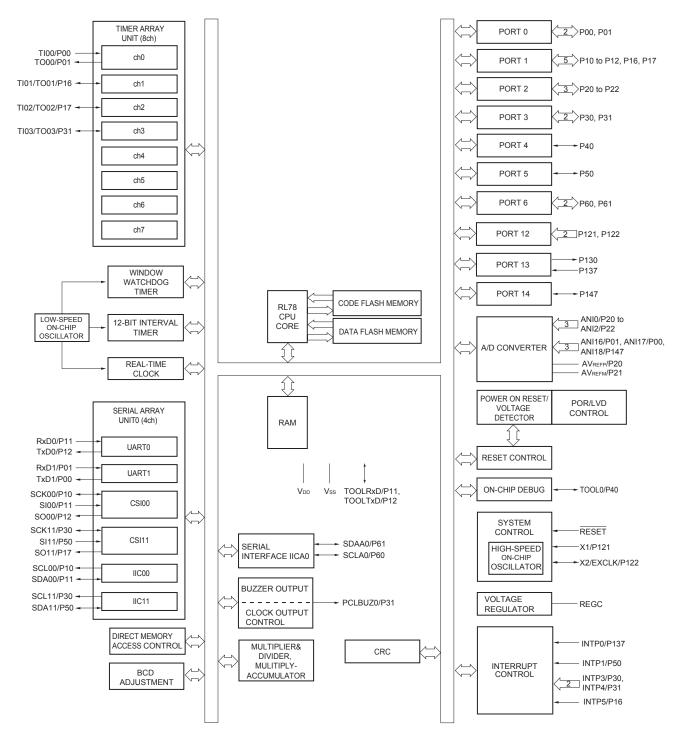
				(10/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	A	R5F100MFAFA#V0, R5F100MGAFA#V0, R5F100MHAFA#V0, R5F100MJAFA#V0, R5F100MKAFA#V0, R5F100MLAFA#V0 R5F100MFAFA#X0, R5F100MGAFA#X0, R5F100MHAFA#X0, R5F100MJAFA#X0, R5F100MKAFA#X0, R5F100MLAFA#X0 R5F100MFDFA#V0, R5F100MGDFA#V0, R5F100MHDFA#V0,
				R5F100MJDFA#V0, R5F100MKDFA#V0, R5F100MLDFA#V0 R5F100MFDFA#X0, R5F100MGDFA#X0, R5F100MHDFA#X0, R5F100MJDFA#X0, R5F100MKDFA#X0, R5F100MLDFA#X0
			G	R5F100MFGFA#V0, R5F100MGGFA#V0, R5F100MHGFA#V0, R5F100MJGFA#V0 R5F100MFGFA#X0, R5F100MGGFA#X0, R5F100MHGFA#X0, R5F100MJGFA#X0
		Not mounted	A	R5F101MFAFA#V0, R5F101MGAFA#V0, R5F101MHAFA#V0, R5F101MJAFA#V0, R5F101MKAFA#V0, R5F101MLAFA#V0 R5F101MFAFA#X0, R5F101MGAFA#X0, R5F101MHAFA#X0, R5F101MJAFA#X0, R5F101MKAFA#X0, R5F101MLAFA#X0
			D	R5F101MFDFA#V0, R5F101MGDFA#V0, R5F101MHDFA#V0, R5F101MJDFA#V0, R5F101MKDFA#V0, R5F101MLDFA#V0 R5F101MFDFA#X0, R5F101MGDFA#X0, R5F101MHDFA#X0, R5F101MJDFA#X0, R5F101MKDFA#X0, R5F101MLDFA#X0
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F100MFAFB#V0, R5F100MGAFB#V0, R5F100MHAFB#V0, R5F100MJAFB#V0, R5F100MKAFB#V0, R5F100MLAFB#V0 R5F100MFAFB#X0, R5F100MGAFB#X0, R5F100MHAFB#X0, R5F100MJAFB#X0, R5F100MKAFB#X0, R5F100MLAFB#X0
			D	R5F100MFDFB#V0, R5F100MGDFB#V0, R5F100MHDFB#V0, R5F100MJDFB#V0, R5F100MKDFB#V0, R5F100MLDFB#V0 R5F100MFDFB#X0, R5F100MGDFB#X0, R5F100MHDFB#X0, R5F100MJDFB#X0, R5F100MKDFB#X0, R5F100MLDFB#X0
			G	R5F100MFGFB#V0, R5F100MGGFB#V0, R5F100MHGFB#V0, R5F100MJGFB#V0 R5F100MFGFB#X0, R5F100MGGFB#X0, R5F100MHGFB#X0, R5F100MJGFB#X0
		Not mounted	A	R5F101MFAFB#V0, R5F101MGAFB#V0, R5F101MHAFB#V0, R5F101MJAFB#V0, R5F101MKAFB#V0, R5F101MLAFB#V0 R5F101MFAFB#X0, R5F101MGAFB#X0, R5F101MHAFB#X0, R5F101MJAFB#X0, R5F101MKAFB#X0, R5F101MLAFB#X0
			D	R5F101MFDFB#V0, R5F101MGDFB#V0, R5F101MHDFB#V0, R5F101MJDFB#V0, R5F101MKDFB#V0, R5F101MLDFB#V0 R5F101MFDFB#X0, R5F101MGDFB#X0, R5F101MHDFB#X0, R5F101MJDFB#X0, R5F101MKDFB#X0, R5F101MLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.5.3 25-pin products





2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^{\circ}C$

R5F100xxAxx, R5F101xxAxx

- D: Industrial applications $T_A = -40$ to $+85^{\circ}C$ R5F100xxDxx, R5F101xxDxx
- G: Industrial applications when $T_A = -40$ to $+105^{\circ}$ C products is used in the range of $T_A = -40$ to $+85^{\circ}$ C

R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.



- **Notes 1.** Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 32 MHz
 - 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8 \text{ V} \le V_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 8 MHz
 - LV (low-voltage main) mode: 1.6 V \leq V_{DD} \leq 5.5 V@1 MHz to 4 MHz
 - 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C



- **Notes 1.** Total current flowing into Vbb, EVbbb, and EVbb1, including the input leakage current flowing when the level of the input pin is fixed to Vbb, EVbb0, and EVbb1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 32 MHz
 - 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $~~1.8~V \leq V_{\text{DD}} \leq 5.5~V @\,1~\text{MHz}$ to 8 MHz
 - LV (low-voltage main) mode: 1.6 V \leq V_DD \leq 5.5 V@1 MHz to 4 MHz
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

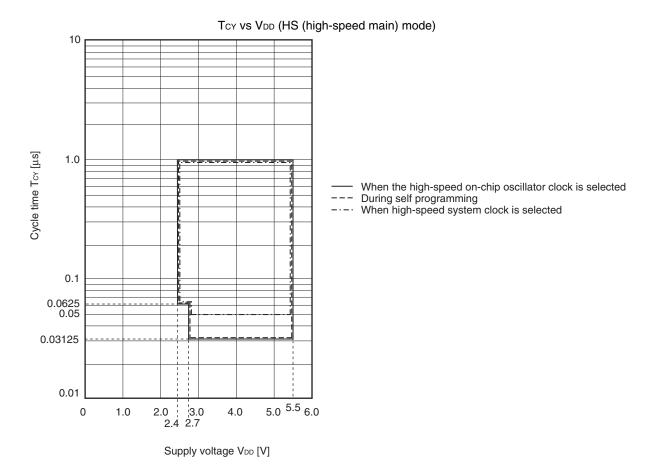


NoteThe following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$ $1.8 V \le EV_{DD0} < 2.7 V : MIN. 125 ns$ $1.6 V \le EV_{DD0} < 1.8 V : MIN. 250 ns$

 $\label{eq:rescaled} \textbf{Remark} \quad \text{f_{MCK}: Timer array unit operation clock frequency}$

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation



R01DS0131EJ0330 Rev.3.30 Mar 31, 2016



Parameter	Symbol	C	Conditions		n-speed Mode	LS (low main)	r-speed Mode	LV (low- main)	Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t ксү1	tксү1 ≥ 4/fclk	$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	125		500		1000		ns
			$\begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	250		500		1000		ns
			$\begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	500		500		1000		ns
			$\begin{array}{l} 1.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	1000		1000		1000		ns
			$\begin{array}{l} 1.6 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$	—		1000		1000		ns
SCKp high-/low-level width	h-/low-level tkH1, $4.0 V \le EV$		5.5 V	tксү1/2 – 12		tксү1/2 – 50		tксү1/2 – 50		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$500 \leq 5.5 \text{ V}$	tксү1/2 – 18		tксү1/2 – 50		tксү1/2 – 50		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DI}}$	$500 \leq 5.5 \text{ V}$	tксү1/2 – 38		tксү1/2 – 50		tксү1/2 – 50		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DI}}$	$500 \leq 5.5 \text{ V}$	tксү1/2 – 50		tксү1/2 – 50		tксү1/2 – 50		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$100 \leq 5.5 \text{ V}$	tксү1/2 – 100		tксү1/2 – 100		tксү1/2 – 100		ns
		$1.6 V \le EV_{DI}$	$500 \leq 5.5 \text{ V}$	—		tксү1/2 – 100		tксү1/2 – 100		ns
SIp setup time	tsik1	$4.0 V \le EV_{DI}$	$100 \leq 5.5 \text{ V}$	44		110		110		ns
(to SCKp↑) Note 1		$2.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$00 \leq 5.5 \text{ V}$	44		110		110		ns
		$2.4 V \le EV_{DI}$	$0.0 \leq 5.5 \text{ V}$	75		110		110		ns
		$1.8 V \le EV_{DI}$	$0.0 \leq 5.5 \text{ V}$	110		110		110		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DI}}$	$0.0 \leq 5.5 \text{ V}$	220		220		220		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DI}}$	5.5 V			220		220		ns
SIp hold time	tksi1	$1.7 \text{ V} \leq \text{EV}_{\text{DI}}$	5.5 V	19		19		19		ns
(from SCKp \uparrow) Note 2		$1.6 \text{ V} \leq \text{EV}_{\text{DI}}$	5.5 V	—		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$\begin{array}{l} 1.7 \ V \leq EV_{DI} \\ C = 30 \ pF^{\text{Note}} \end{array}$			25		25		25	ns
output Note 3		$1.6 V \le EV_{DI}$ C = 30 pF ^{Note}			_		25		25	ns

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) ($T_4 = -40$ to $+85^{\circ}$ C, 1.6 V \leq EVppa = EVpp1 \leq Vpp \leq 5.5 V, Vss = EVssa = EVssa = 0 V)

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Unit

ns

60

130

tput,

(7) Communica correspond		-	ntial (2.5 V, 3 V) (CSI	mode) (I	naster	mode, S	СКр і	internal	clock ou	tı
(TA = -40 to Parameter	+85°C, 2 Symbol	5° C, 2.7 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVssoymbolConditionsHS (high-speed main) Mode		h-speed	LS (lov	= 0 V) /-speed Mode	LV (low-voltage main) Mode			
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tксү1 ≥ 2/fc∟к	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \\ k\Omega \end{array}$	200		1150		1150		
			$\begin{split} & 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 20 \ pF, \ R_b = 2.7 \\ & k\Omega \end{split}$	300		1150		1150		
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \\ 2.7 \ V \leq V_b \leq \\ C_b = 20 \ pF, \ F \end{array}$	4.0 V,	tксү1/2 – 50		tксү1/2 – 50		tксү1/2 – 50		
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} \\ 2.3 \ V \leq V_b \leq \\ C_b = 20 \ pF, \ F \end{array}$	2.7 V,	tксү1/2 – 120		tксү1/2 – 120		tксү1/2 – 120]
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \\ 2.7 \ V \leq V_b \leq \\ C_b = 20 \ pF, \ F \end{array}$	4.0 V,	tксү1/2 – 7		tксү1/2 – 50		t _{ксү1} /2 – 50		
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} \\ 2.3 \ V \leq V_b \leq \\ C_b = 20 \ pF, \ F \end{array}$	2.7 V,	tксү1/2 – 10		tксү1/2 – 50		tксү1/2 – 50		
SIp setup time (to SCKp↑) ^{№te 1}	tsıĸı	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \\ 2.7 \ V \leq V_b \leq \\ C_b = 20 \ pF, \ F \end{array}$	4.0 V,	58		479		479		
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} \\ 2.3 \ V \leq V_b \leq \\ C_b = 20 \ pF, \ F \end{array}$	2.7 V,	121		479		479		
Slp hold time	tksi1	$4.0 V \le EV_{DD}$	$0 \le 5.5 V$,	10		10		10		Ī

(Notes, Caution, and Remarks are listed on the next page.)

 $2.7~V \leq V_b \leq 4.0~V,$

 $2.3~V \leq V_b \leq 2.7~V,$ $C_b = 20 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$ $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$

 $2.7~V \leq V_{b} \leq 4.0~V,$

 $2.3~V \leq V_b \leq 2.7~V,$ $C_b = 20 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$

 $C_{\text{b}}=20 \text{ pF}, \text{ R}_{\text{b}}=1.4 \text{ k}\Omega$ $2.7 V \le EV_{DD0} < 4.0 V$,

 $C_b = 20 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$ $2.7 V \le EV_{DD0} < 4.0 V$,

(from SCKp↑) Note 1

Delay time from

 $\mathsf{SCKp}{\downarrow} \text{ to } \mathsf{SOp}$

output Note 1

tks01



10

60

130

10

60

130

10

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

Parameter	Symbol	Conditions		h-speed Mode	``	/-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 1}	tsıkı	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	44		110		110		ns
		$\label{eq:cb} \begin{split} C_b &= 30 \; pF, \; R_b = 1.4 \; k\Omega \\ 2.7 \; V &\leq EV_{\text{DD0}} < 4.0 \; V, \\ 2.3 \; V &\leq V_b \leq 2.7 \; V, \end{split}$	44		110		110		ns
		C_b = 30 pF, R_b = 2.7 k Ω							
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	110		110		110		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=5.5 \text{k}\Omega$							
SIp hold time (from SCKp↓) ^{№ te 1}	tksii	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	19		19		19		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=1.4 \text{k}\Omega$							
		$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \\ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \end{array}$	19		19		19		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=2.7 \text{k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	19		19		19		ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=5.5 \text{k}\Omega$							
Delay time from SCKp↑ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		25		25		25	ns
SOp output Note 1		$C_{b}=30 \text{ pF}, \text{R}_{b}=1.4 \text{k}\Omega$							
		$\begin{array}{l} 2.7 \ V \leq EV_{\rm DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_{\rm b} \leq 2.7 \ V, \end{array}$		25		25		25	ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=2.7 \text{k}\Omega$							
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$		25		25		25	ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=5.5 \text{k}\Omega$							

		5 5 V Voo - EVo	$ = EV_{oot} = 0.V$
$T_{A} = -40$ to +85°C,		j.j v, vss = ⊑vs	$s_0 = \Box v s s_1 = U v $

Notes 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol		<u>≤ Vod ≤ 5.5 V, Vss =</u> nditions	HS (speed	high- main) de	LS (low			-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}		$4.0 V \le EV_{DD0} \le 5.5 V$, $2.7 V \le V_b \le 4.0 V$	24 MHz < fмск	14/ fмск				_		ns
			20 MHz < fмск ≤ 24 MHz	12/ fмск		_		—		ns
			8 MHz < fмск ≤ 20 MHz	10/ fмск						ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/ fмск				ns
			fмск ≤4 MHz	6/f мск		10/ fмск		10/ fмск		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	24 MHz < fмск	20/ fмск				_		ns
			20 MHz < fмск ≤ 24 MHz	16/ fмск				—		ns
			16 MHz < fмск ≤ 20 MHz	14/ fмск				_		ns
			8 MHz < fмск ≤ 16 MHz	12/ fмск						ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/ fмск				ns
			fмск ≤4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		$\begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note}} \end{split}$	24 MHz < fмск	48/ fмск		_		—		ns
		2	20 MHz < fмск ≤ 24 MHz	36/ fмск		_				ns
			16 MHz < fмск ≤ 20 MHz	32/ fмск		—		_		ns
			8 MHz < fмск ≤ 16 MHz	26/ fмск		_		_		ns
			4 MHz < fмск ≤ 8 MHz	16/ fмск		16/ fмск		_		ns
			fмск ≤4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions		high- main) ode	LS (low	· · ·	•	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	tкн2, tкL2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$	tксү2/2 – 12		tксү2/2 - 50		tксү2/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	tксү2/2 – 18		tксү2/2 - 50		tксү2/2 - 50		ns
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq E V_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{split}$	tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 3}	tsik2	$\begin{array}{l} 4.0 \; V \leq E V_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{array}{l} 2.7 \ V \leq E V_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{array}$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	tksi2		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 5	tkso2	$\label{eq:V_def} \begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \\ V, \\ C_{\text{b}} = 30 \ pF, \ R_{\text{b}} = 1.4 \ k\Omega \end{array}$		2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
		$\label{eq:V_def} \begin{array}{l} 2.7 \; V \leq EV_{\text{DD0}} < 4.0 \; V, \; 2.3 \; V \leq V_{b} \leq 2.7 \\ V, \\ C_{b} = 30 \; pF, \; R_{b} = 2.7 \; k\Omega \end{array}$		2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.



Parameter	Symbol			LS (low-speed main) Mode			-voltage Mode	Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat		1/fмск + 135 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
		$\label{eq:V} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 135 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
			1/fмск + 190 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
		$\label{eq:linear} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 190 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
		$ \begin{split} & 1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split} $	1/f _{MCK} + 190 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
			0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:VDD} \begin{split} & 1.8 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \\ & 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ & C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	0	405	0	405	0	405	ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2) (T_A = -40 to +85°C. 1.8 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V. Vss = EV_{SS0} = EV_{SS1} = 0 V)

Notes 1. The value must also be equal to or less than f_MCK/4.

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.



3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$ R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 - 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see **CHAPTER 2 ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Application						
	A: Consumer applications, D: Industrial applications	G: Industrial applications					
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C					
Operating mode Operating voltage range	$\begin{array}{l} \text{HS (high-speed main) mode:} \\ \text{2.7 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 32 MHz} \\ \text{2.4 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 16 MHz} \\ \text{LS (low-speed main) mode:} \\ \text{1.8 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 8 MHz} \\ \text{LV (low-voltage main) mode:} \\ \text{1.6 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 4 MHz} \end{array}$	HS (high-speed main) mode only: 2.7 V \leq V _{DD} \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq V _{DD} \leq 5.5 V@1 MHz to 16 MHz					
High-speed on-chip oscillator clock accuracy	$\begin{array}{l} 1.8 \ V \leq V_{DD} \leq 5.5 \ V \\ \pm 1.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 1.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \\ 1.6 \ V \leq V_{DD} < 1.8 \ V \\ \pm 5.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 5.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \end{array}$	$\begin{array}{l} 2.4 \ V \leq V_{DD} \leq 5.5 \ V \\ \pm 2.0\% @ \ T_{A} = +85 \ to \ +105^{\circ}C \\ \pm 1.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 1.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \end{array}$					
Serial array unit	UART CSI: fcLk/2 (supporting 16 Mbps), fcLk/4 Simplified I ² C communication	UART CSI: fcLk/4 Simplified I ² C communication					
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode					
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)					



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{∾te 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \leq EV_{DD0} \leq 5.5~V$			-3.0 Note 2	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-30.0	mA
	P125 to P127, P130, P140 to P145 (When duty $\leq 70\%^{Note 3}$) Total of P05, P06, P10 to P17, P30, P31,		$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
			$2.4~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80				-30.0	mA
			$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
		$2.4~V \leq EV_{DD0} < 2.7~V$			-10.0	mA	
			$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	2,4 V \leq V_{DD} \leq 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
 - Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80% and $I_{OH} = -10.0 \text{ mA}$
 - Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVDD0				1	μA
	Ілна	P20 to P27, P137, P150 to P156, RESET	$V_{I} = V_{DD}$	$V_{I} = V_{DD}$			1	μA
	Іцнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	1.1.1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso				-1	μA
	Ilile	P20 to P27, P137, P150 to P156, RESET	VI = Vss				-1	μA
	Ililis	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pll-up resistance	Ru	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVsso	, In input port	10	20	100	kΩ

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (5/5)

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply IDD1 current Note 1	Idd1	Operating mode	HS (high- speed main) mode ^{Note 5}	f _{IH} = 32 MHz ^{Note 3}	Basic operatio n	V _{DD} = 5.0 V V _{DD} = 3.0 V		2.3 2.3		mA mA
					Normal operatio	V _{DD} = 5.0 V V _{DD} = 3.0 V		5.2 5.2	9.2 9.2	mA mA
				fin = 24 MHz ^{Note 3}	n Normal operatio	V _{DD} = 5.0 V V _{DD} = 3.0 V		4.1 4.1	7.0 7.0	mA mA
				fін = 16 MHz ^{№оtе 3}	n Normal	$V_{DD} = 5.0 V$		3.0	5.0	mA
					operatio n	$V_{DD} = 3.0 V$		3.0	5.0	mA
			HS (high- speed main)	$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.4	5.9	mA
			mode ^{Note 5}	V _{DD} = 5.0 V	operatio n	Resonator connection		3.6	6.0	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$	Normal operatio n	Square wave input Resonator		3.4 3.6	5.9 6.0	mA mA
				fмx = 10 MHz ^{Note 2} ,	Normal	connection Square wave input		2.1	3.5	mA
				$V_{DD} = 5.0 V$	operatio n	Resonator connection		2.1	3.5	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		2.1	3.5	mA
				V _{DD} = 3.0 V	operatio n	Resonator connection		2.1	3.5	mA
		Subsystem clock	fsub = 32.768 kHz	Normal operatio	Square wave input Resonator		4.8	5.9	μA	
			operation	T _A = -40°C	n	connection		4.9	6.0	μA
				fsub = 32.768 kHz Note 4	Normal operatio	Square wave input Resonator		4.9 5.0	5.9 6.0	μA μA
				$T_A = +25^{\circ}C$	n Nama l	connection		5.0	7.0	
				$f_{SUB} = 32.768 \text{ kHz}$ Note 4 $T_A = +50^{\circ}\text{C}$	Normal operatio n	Square wave input Resonator connection		5.0 5.1	7.6 7.7	μΑ μΑ
				fsub = 32.768 kHz	3 = 32.768 kHz Normal	Square wave input		5.2	9.3	μA
				Note 4 $T_A = +70^{\circ}C$	operatio n	Resonator connection		5.3	9.4	μA
				fsub = 32.768 kHz	Normal	Square wave input		5.7	13.3	μA
				T _A = +85°C	operatio n	Resonator connection		5.8	13.4	μA
				fsub = 32.768 kHz	Normal operatio	Square wave input Resonator		10.0 10.0	46.0 46.0	μA μA
				T _A = +105°C	n	connection		10.0	40.0	μη

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products	
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/2)	

(Notes and Remarks are listed on the next page.)



Parameter	Symbol	Conditions	HS (high-speed ma Mode) Unit	
			MIN.	MAX.		
SCLr clock frequency	fscL	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$		400 Note1	kHz	
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$				
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$		100 Note1	kHz	
		$C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{k}\Omega$				
Hold time when SCLr = "L"	t∟ow	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1200		ns	
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$				
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	4600		ns	
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$				
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1200		ns	
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$				
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	4600		ns	
		$C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{k}\Omega$				
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	1/fмск + 220 Note2		ns	
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$	Note2			
		$2.4~V \leq EV_{\text{DD}} \leq 5.5~V,$	1/fмск + 580 Note2		ns	
		$C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{k}\Omega$	Note2			
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$	0	770	ns	
		$C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$				
		$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V,$	0	1420	ns	
		$C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{k}\Omega$				

(4) During communication at same potential (simplified l²C mode) (T_A = -40 to +105°C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

- Notes 1. The value must also be equal to or less than $f_{MCK}/4$.
 - **2.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

Parameter Sy	Symbol		Condit	Conditions		HS (high-speed main) Mode	
						MAX.	
Transfer rate		Transmission	$4.0~V \leq EV_{\text{DD0}} \leq 5.5$		Note 1	bps	
			V, $2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate		2.6 Note 2	Mbps
				$\begin{array}{l} C_{b}=50 \; pF, \; R_{b}=1.4 \; k\Omega, \; V_{b}=2.7 \\ V \end{array} \label{eq:cb}$			
		V,	$2.7 V \leq EV_{DD0} < 4.0$		Note 3	bps	
			V, $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3$		1.2 Note 4	Mbps
	V,	2.4 V ≤ EV _{DD0} < 3.3	V		Note 5	bps	
		V, $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6$ V		0.43 Note 6	Mbps	

Notes 1. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV _DD0 \leq 5.5 V and 2.7 V \leq V _b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

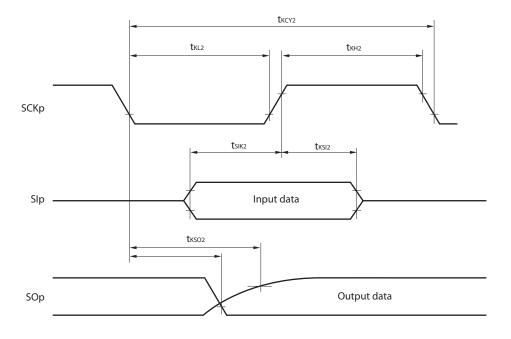
Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

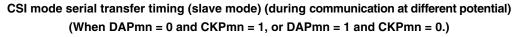
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

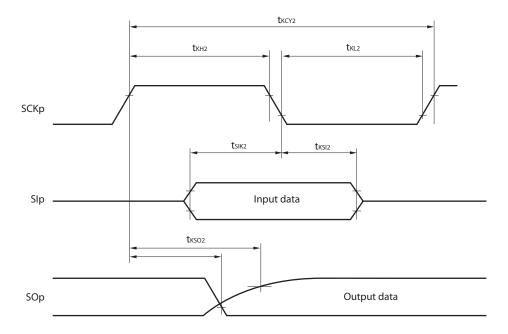
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,

n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

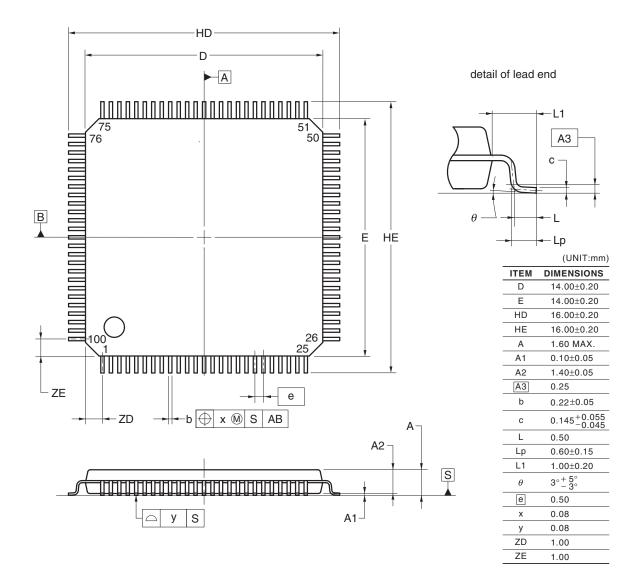
2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



4.13 100-pin Products

R5F100PFAFB, R5F100PGAFB, R5F100PHAFB, R5F100PJAFB, R5F100PKAFB, R5F100PLAFB R5F101PFAFB, R5F101PGAFB, R5F101PHAFB, R5F101PJAFB, R5F101PKAFB, R5F101PLAFB R5F100PFDFB, R5F100PGDFB, R5F100PHDFB, R5F100PJDFB, R5F100PKDFB, R5F100PLDFB R5F101PFDFB, R5F101PGDFB, R5F101PHDFB, R5F101PJDFB, R5F101PKDFB, R5F101PLDFB R5F100PFGFB, R5F100PGGFB, R5F100PHGFB, R5F100PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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